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(Approved by AICTE, New Delhi & Govt. of Karnataka)

(Autonomous Institute, Affiliated to VTU)
Accredited by NBA & NAAC with 'A' Grade**SEMESTER END EXAMINATIONS FEBRUARY - MARCH 2021**

Program	: B.E. : Electronics and Communication Engineering	Semester	: III
Course Name	: Analog Circuits	Max. Marks	: 100
Course Code	: EC32	Duration	: 3 Hrs

Instructions to the Candidates:

- Answer one full question from each unit.

UNIT- I

1. a) Find V_y using mesh current analysis for the circuit as shown in CO1 (10)
Fig.1(a).

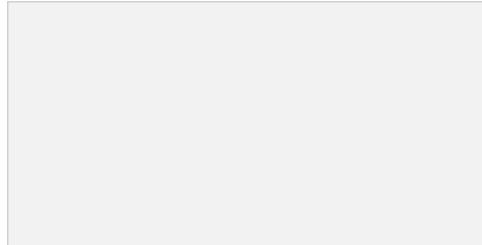


Fig.1(a)

- b) Convert the given circuit as shown in Fig.1(b) into a current source in parallel with a resistor across A - B.

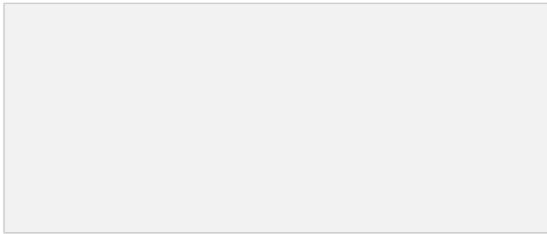


Fig.1(b)

2. a) Find the equivalent resistance between terminals AB using star - delta transformation for the network as shown in Fig.2(a).

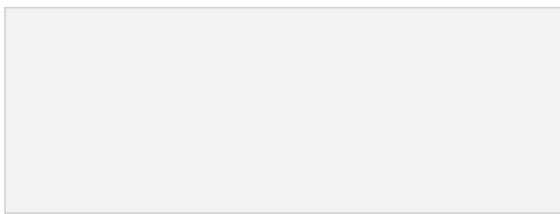


Fig.2(a)

- b) Using nodal analysis find i_1 and i_3 currents in the circuit shown in CO1 (10)
Fig.2(b).

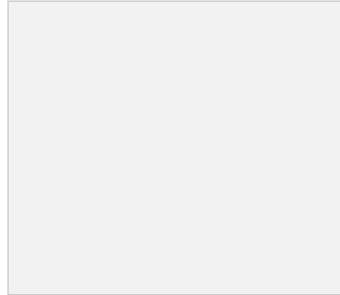
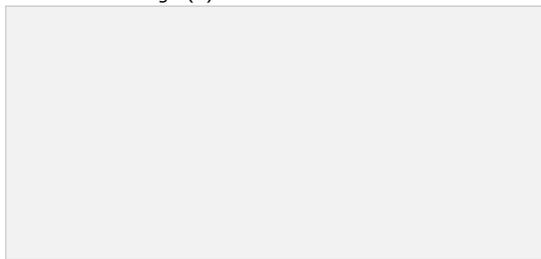


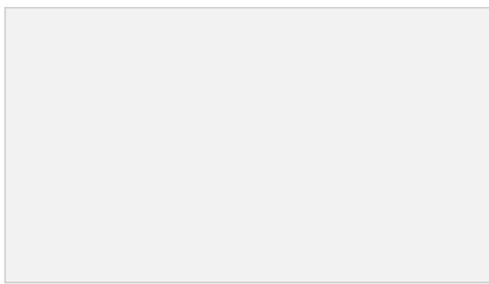
Fig.2(b)

UNIT - II

3. a) State and Prove Superposition theorem. CO2 (10)
b) Find the thevenin's equivalent network which includes a dependent CO2 (10)
source as shown in Fig.3(b).



4. a) State and prove thevenin's theorem. CO2 (10)
b) For the circuit as shown in Fig.4(b), find the value of R_L which CO2 (10)
results in maximum power transfer. Also calculate the value of the
maximum power.

**UNIT - III**

5. a) State the advantages and disadvantages of h-parameters and draw the small signal model of CE amplifier. CO3 (05)
- b) Show that negative feedback decreases the output resistance of voltage series feedback amplifier. CO3 (06)
- c) The transistor with $h_{ie}=1\text{k}\Omega$, $h_{fe}=60$, $h_{re}=205\times10^{-4}$, $h_{oe}=25\times10^{-6}$ A/V, is connected in CE configuration as shown in Fig.5(c). Calculate: $A_i = I_o/I_i$, A_v , R_i , R_o .

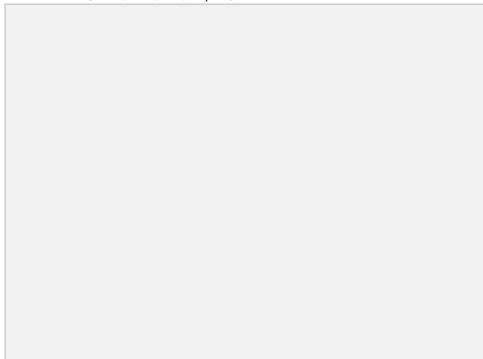


Fig.5(c)

6. a) The transistor used in the circuit as shown in Fig.6(a) has the following parameters, $h_{re}=60$, $h_{ie}=500\Omega$, $h_{oe}=1/40\text{K}$ and $h_{re}=2.4\times10^{-4}$. Calculate R_i , R_o , A_i , A_v and A_{vs} . CO3 (09)

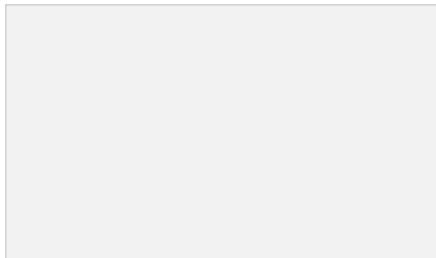


Fig.6(a)

EC32

- b) A voltage amplifier has the following parameter values without feedback. CO3 (06)

Open circuit voltage gain $A_v = -500$

Input resistance $R_i = 2 \text{ k}\Omega$

Output resistance $R_o = 402 \text{ k}\Omega$

Bandwidth $BW = 300\text{KHz}$

Load resistance $R_L = 10\text{KHz}$

If 10% negative voltage series feedback is given. Calculate A_{vf} , R_{if} and BW_f .

- c) State and prove Miller's Dual theorem. CO3 (05)

UNIT - IV

7. a) Derive an expression for the output power and conversion efficiency of a transformer coupled class B push pull power amplifier. CO4 (08)

- b) With neat sketches explain the thermal analogy of a power transistor. CO4 (04)

- c) Design a single ended class A power amplifier and draw the circuit with proper design components to meet the following specifications. CO4 (08)

i) Maximum 400mW to be delivered to a load of 8Ω

ii) Transformer efficiency of 80%

iii) Power supply available of 7V

Transistors available

i) SL100 with $(P_d)_{max} = 500\text{mW}$

ii) 2N 176 with $(P_d)_{max} = 10\text{W}$

iii) 40309 with $(P_d)_{max} = 2.5\text{W}$

8. a) State the heat sink selection criterion for a transistor operating with $V_{CE} = 20\text{V}$ and $I_C = 1.5\text{A}$. Its thermal resistance from junction to case is $1^\circ\text{C}/\text{W}$. The junction temperature should not exceed 85°C if the ambient temperature is 25°C . CO4 (07)

- b) With neat sketches explain the operation of class C power amplifier. CO4 (08)

- c) A power amplifier has harmonic distortions $D_2 = 0.1$, $D_3 = 0.02$, $D_4 = 0.01$, the fundamental current $I_1 = 4\text{A}$ and $R_L = 8\Omega$. Calculate the total harmonic distortion, fundamental power and total power. CO4 (05)

UNIT - V

9. a) Explain the V-I characteristics of an N-channel E-MOSFET with neat sketches? CO5 (06)

- b) To establish a dc current $I_D = 0.5\text{mA}$, the MOSFET is specified to have $V_T = 1\text{V}$, $K_n W/L = 1\text{mA/V}^2$, $\lambda = 0$, $V_{DD} = 15\text{V}$. Calculate %change in I_D when MOSFET is replaced having the same $K_n W/L$ but $V_T = 1.5\text{V}$ as shown in Fig.9(b) CO5 (10)